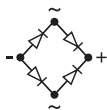


CBR1-D010 SERIES**SILICON BRIDGE RECTIFIER
1 AMP, 100 THRU 1000 VOLTS****DIP CASE**www.centrasemi.com**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBR1-D010 series types are full wave silicon bridge rectifiers mounted in a durable epoxy molded case. These devices are ideal for printed circuit board mounting and fit into a standard DIP socket (0.1"/2.54mm spacing).

NOTE: Also available in fast recovery. Please contact factory for details.

MARKING: FULL PART NUMBER**MAXIMUM RATINGS:** ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	CBR1 -D010	CBR1 -D020	CBR1 -D040	CBR1 -D060	CBR1 -D080	CBR1 -D100	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_A=50^{\circ}\text{C}$)	I_O				1.0			A
Peak Forward Surge Current	I_{FSM}				50			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150				$^{\circ}\text{C}$

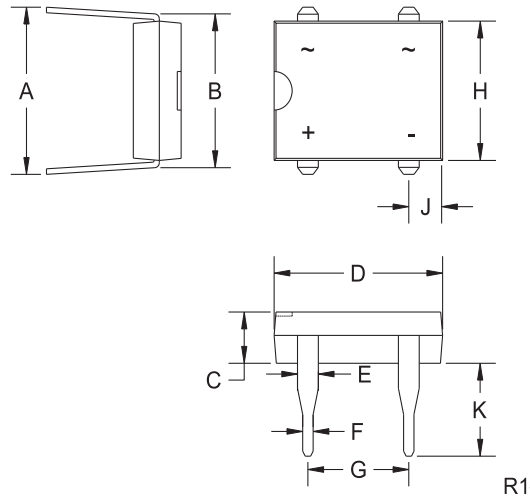
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		10	μA
V_F	$I_F=1.0\text{A}$		1.1	V

CBR1-D010 SERIES
SILICON BRIDGE RECTIFIER
1 AMP, 100 THRU 1000 VOLTS



DIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.300	0.350	7.62	8.89
B	0.285	0.315	7.24	8.00
C	0.086	0.098	2.18	2.49
D	0.316	0.335	8.03	8.51
E	0.035	0.045	0.89	1.14
F	0.018	0.022	0.46	0.56
G	0.195	0.205	4.95	5.21
H	0.245	0.255	6.22	6.48
J	0.055	0.075	1.40	1.91
K	0.150	0.185	3.81	4.70

DIP (REV: R1)

MARKING: FULL PART NUMBER

R3 (11-June 2012)